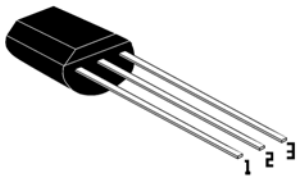
CHANG JIANG
ELECTRONICS CO., LTD.

8550

低压晶体管

- 高集电极电流 Ic=-1200mA
- 高耗散功率 Pc=1000mW
- 与 8050 对管

TO-92



1：Emiter
2：Base
3：Collector

极限参数(Absolute Maximum Ratings) Ta=25^{0}C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	**-40**	V
Collector-Emitter Voltage	Vceo	**-25**	V
Emitter-Base Voltage	Vebo	**-6**	V
Collector Current	Ic	**-1200**	mA
Collector Dissipation	Pc	**1000**	m W
Junction Temperature	Tj	**150**	^{0}C
Storage Temperature	Tstg	**-55~150**	^{0}C

电性能(Electrical Characteristic) Ta=25^{0}C

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BVcbo	Collector-Base Breakdown Voltage	Ic=-100uA Ie=0	-40			V
BVceo	Collector-Emitter Breakdown Voltage	Ic=-2mA Ib=0	-25			V
BVebo	Emitter-Base Breakdown Voltage	Ie=-100uA Ic=0	-6			V
Icbo	Collector Cutoff Current	Vcb=-35V, Ie=0			-100	nA
Iebo	Emitter Cutoff Current	Veb=-6V, Ic=0			-100	nA
Iceo	Collector Cutoff Current	Vce=-25V, Ib=0			-10	uA
Vce(sat)	Collector-Emitter Saturation Voltage	Ic=-800mA, Ib=-80mA		-0.26	-0.5	V
Vbe(sat)	Base-Emitter Saturation Voltage	Ic=-800mA, Ib=-80mA		-0.98	-1.2	V
Vbe(on)	Base-Emitter On Voltage	Vce=-1V, Ic=-10mA		-0.66	-1	V
Hfe1	DC Current Gain	Vce=-1V, Ic=-5mA	45			
Hfe2	DC Current Gain	Vce=-1V, Ic=-100mA	85		400	
Hfe3	DC Current Gain	Vce=-1V, Ic=-800mA	30			
Cob	Output Capacitance	Vcb=10V, Ie=0,f=1MHz		9	15	PF
fT	Current Gain-Bandwidth product	Vce=10V, Ic=50mA,	100	200		MHz

CLASS	B	C	D				
Hfe2	85-120	120-160-200	160-200	200-250	250-300	300-350	350-400